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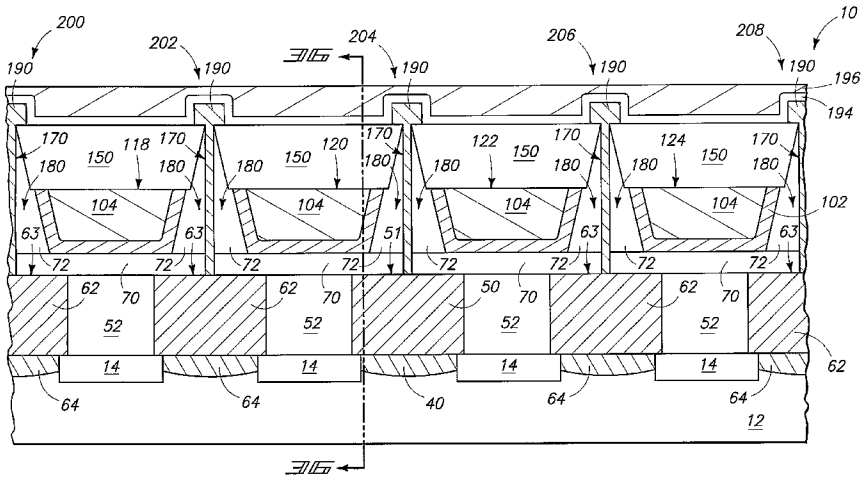
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(54) Title: MEMORY ARRAYS; METHODS OF FORMING MEMORY ARRAYS; AND METHODS OF FORMING CONTACTS TO BITLINES



(57) Abstract: The invention includes memory arrays, and methods which can be utilized for forming memory arrays. A patterned etch stop /70) can be used during memory array fabrication, with the etch stop covering storage node contact locations (46,50) while leaving openings to bitline contact locations (48). An insulative material (72) can be formed over the etch stop and over the bitline contact locations, and trenches can be formed through the insulative material. Conductive material can be provided within the trenches to form bitline interconnect lines (102,104) which are in electrical contact with the bitline contact locations, and which are electrically isolated from the storage node contact locations by the etch stop. In subsequent processing, openings can be formed through the etch stop to the storage node contact locations. Memory storage devices (190,194,196) can then be formed within the openings and in electrical contact with the storage node contact locations.

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